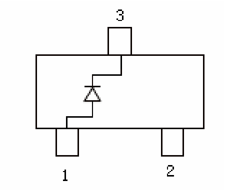
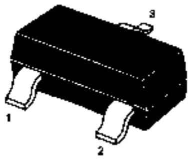
BAS20 SWITCHING DIODE



FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance



Marking: JR

SOT-23

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage **DC Blocking Voltage**	V_{RM} V_R	150	V
Average Rectified Output Current	I_O	200	mA
Power Dissipation	Pd	250	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta}JA$	500	℃/W
Junction temperature	T_J	150	℃
Storage temperature range	T_{STG}	-65-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)\,R}$	I_R= 100μA	150		V
Reverse voltage leakage current	I_R	VR=150V		0.1	μA
Forward voltage	V_F	I_F=100mA I_F=200mA		1 1.25	V
Junction Capacitance	C_J	V_R=0V, f=1MHz		5	pF
Reveres recovery time	t_{rr}	I_F=I_R=30mA, I_{rr}=0.1×I_R		50	nS

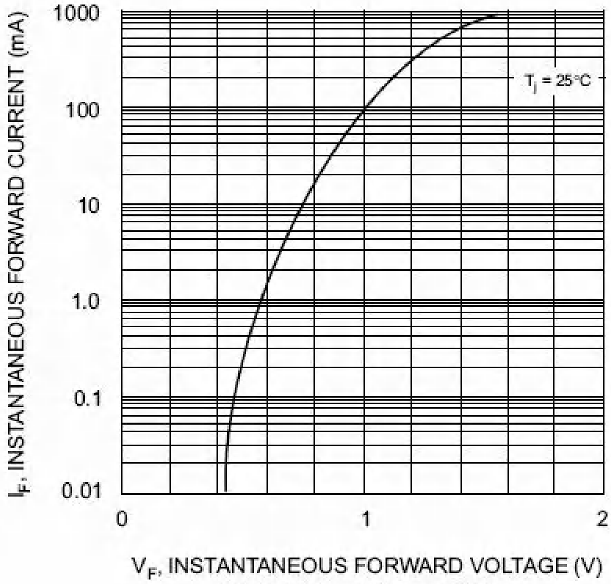


Fig. 1 Forward Characteristics

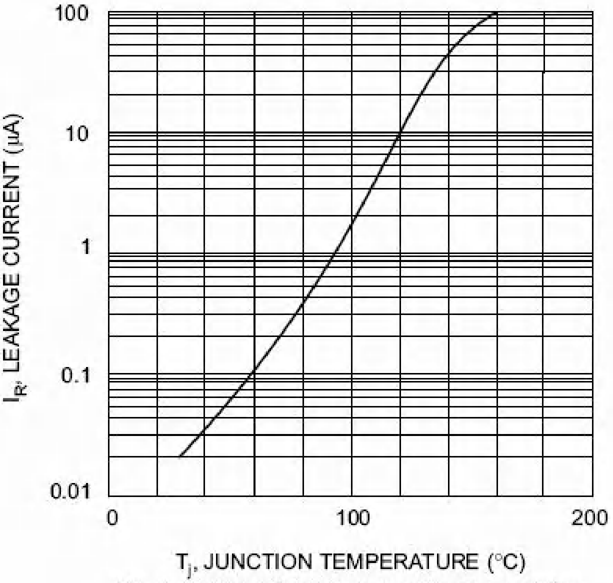
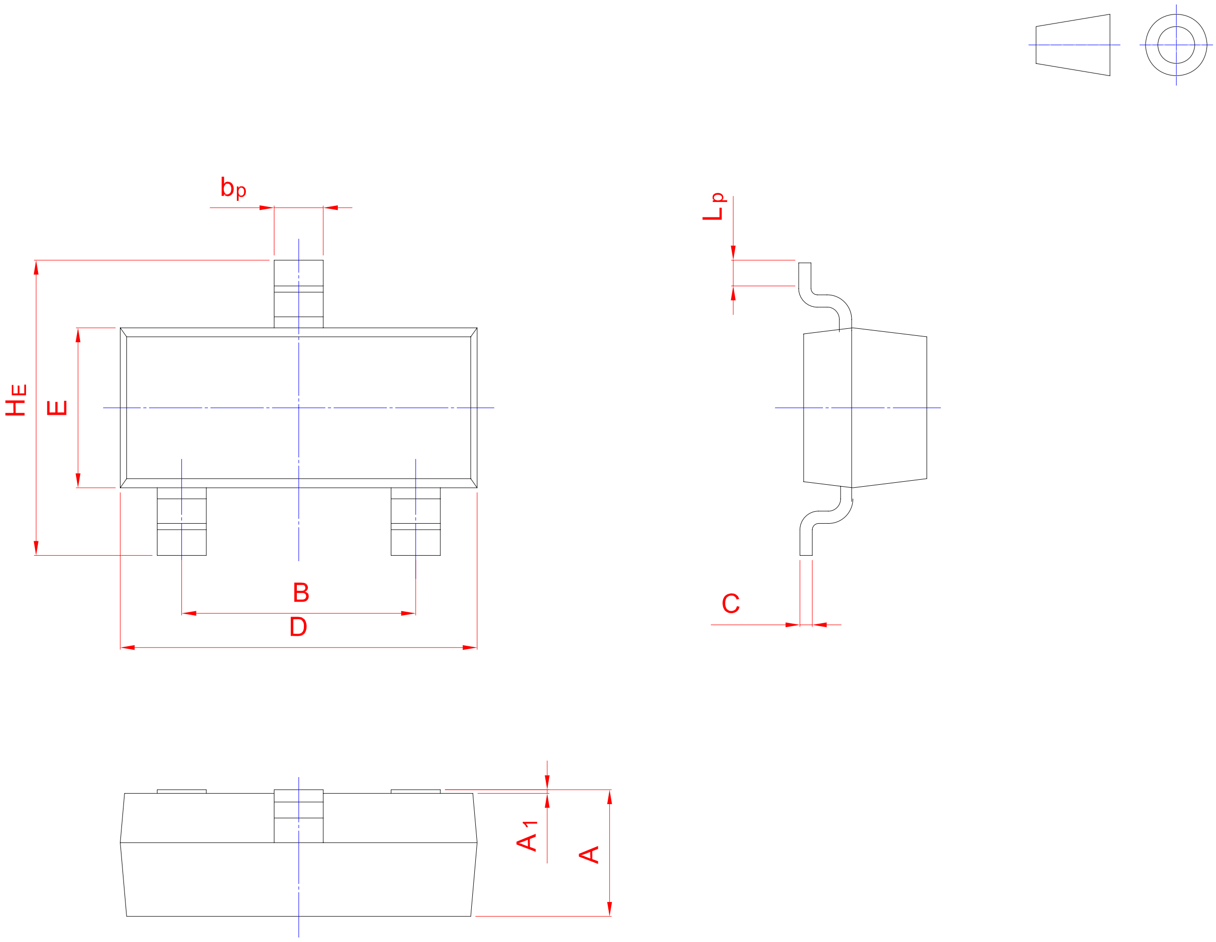


Fig. 2 Leakage Current vs Junction Temperature

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20